

Revision History**16M** (1M x 16 bit) PSEUDO STATIC RAM**48ball FPBGA Package**

Revision	Details	Date
Rev 1.0	Preliminary datasheet	Aug 2018

1Mb x16 Pseudo Static RAM Specification

GENERAL DESCRIPTION

The AS1C1M16P-70BIN is 16,777,216 bits of Pseudo SRAM which uses DRAM type memory cells, but this device has refresh-free operation and extreme low power consumption technology. Furthermore the interface is compatible to a low power Asynchronous type SRAM. The AS1C1M16P-70BIN is organized as 1,048,576 Words x 16 bit.

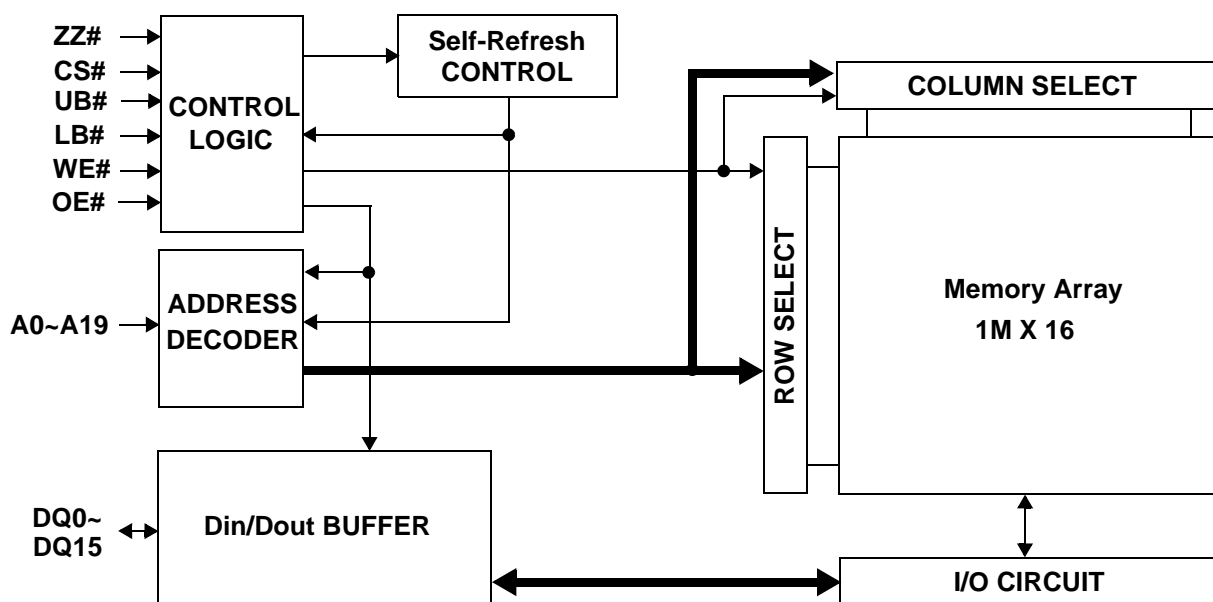
FEATURES

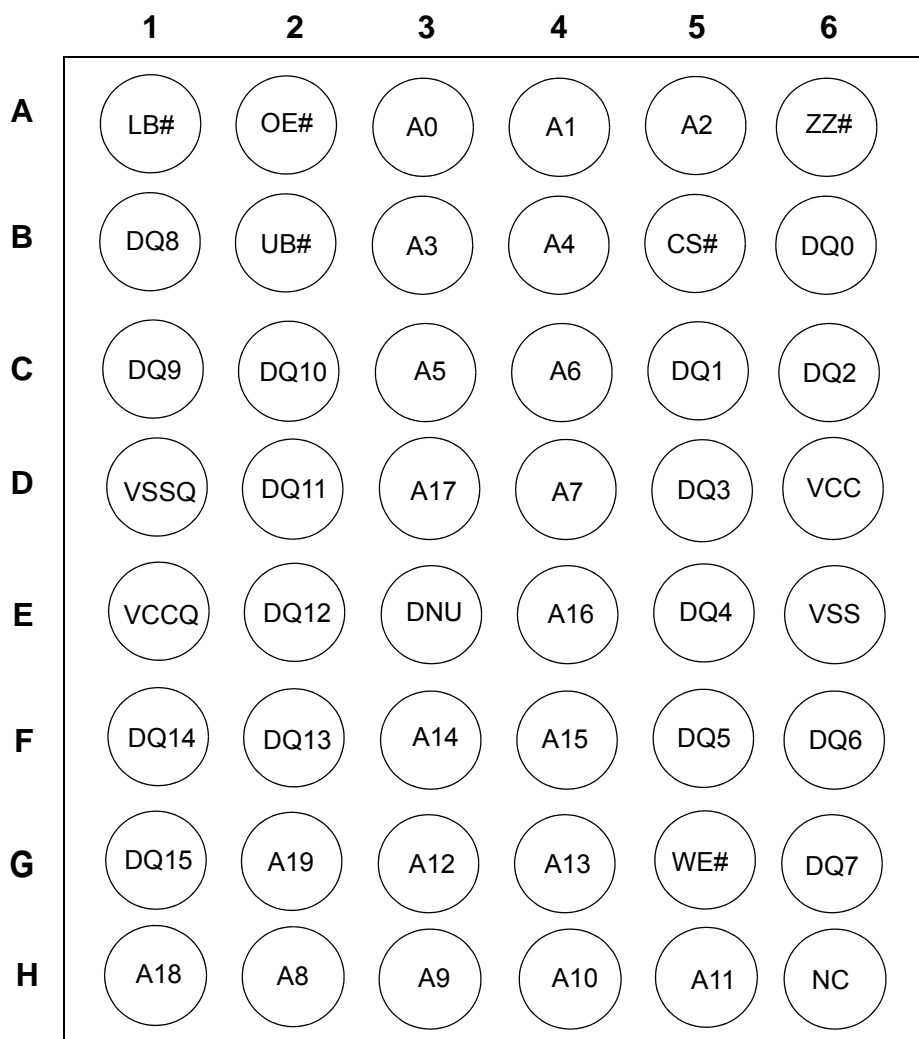
- Organization : 1M x16
- Address access speed 70ns
- Power Supply Voltage : 2.6 ~ 3.3V
- Separated I/O power(VccQ) & Core power(Vcc)
- Three state outputs
- Byte read/write control by UB# / LB#
- Auto-TCSR for power saving
- Package type : 48ball-FPBGA (6.0x7.0)
- Operating Temperature
- . Industrial : -40 °C ~ 85 °C

PRODUCT FAMILY

Part Number	Operating Temp.	Power Supply	Speed (t _{RC})	Power Dissipation		
				Standby (I _{SB} , Max.)	Operating I _{CC} (Max.)	
					I _{CC1} (f = 1MHz)	I _{CC2} (f = f _{max})
AS1C1M16P-70BIN	-40°C to 85°C	2.6 ~ 3.3V	70ns	120uA	5mA	25mA

FUNCTION BLOCK DIAGRAM



PIN DESCRIPTION(48-FPBGA-6.00 x 7.00)

TOP VIEW (Ball Down)

Name	Function	Name	Function
CS#	Chip select input	LB#	Lower byte (DQ ₀₋₇)
OE#	Output enable input	UB#	Upper byte (DQ ₈₋₁₅)
WE#	Write enable input	VCC	Power supply
ZZ#	Connected with VCC in this version	VCCQ	I/O power supply
DQ ₀₋₁₅	Data in-out	VSS(Q)	Ground
A ₀₋₁₉	Address inputs	NC	No connection
DNU	Do not use		

ABSOLUTE MAXIMUM RATINGS ¹⁾

Parameter	Symbol	Ratings	Unit
Voltage on Any Pin Relative to V _{SS}	V _{IN} , V _{OUT}	-0.2 to V _{CCQ} +0.3V	V
Voltage on V _{CC} supply relative to V _{SS}	V _{CC} , V _{CCQ}	-0.2 ²⁾ to V _{CCQ} +0.3V	V
Power Dissipation	P _D	1.0	W
Storage Temperature	T _{STG}	-65 to 150	°C
Operating Temperature	T _A	-40 to 85	°C

- Stresses greater than those listed above “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- Undershoot at power-off : -1.0V in case of pulse width ≤ 20ns

FUNCTIONAL DESCRIPTION

CS#	OE#	WE#	LB#	UB#	DQ ₀₋₇	DQ ₈₋₁₅	Mode	Power
H	X	X	X	X	High-Z	High-Z	Deselected	Stand by
L	H	H	L	X	High-Z	High-Z	Output Disabled	Active
L	H	H	X	L	High-Z	High-Z	Output Disabled	Active
L	L	H	L	H	Data Out	High-Z	Lower Byte Read	Active
L	L	H	H	L	High-Z	Data Out	Upper Byte Read	Active
L	L	H	L	L	Data Out	Data Out	Word Read	Active
L	X	L	L	H	Data In	High-Z	Lower Byte Write	Active
L	X	L	H	L	High-Z	Data In	Upper Byte Write	Active
L	X	L	L	L	Data In	Data In	Word Write	Active

Note:

- X means don't care. (Must be low or high state)

RECOMMENDED DC OPERATING CONDITIONS ¹⁾

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	2.6	3.0	3.3	V
	V_{CCQ}	2.6	3.0	3.3	V
Ground	V_{SS}, V_{SSQ}	0	0	0	V
Input high voltage	V_{IH}	$0.8 * V_{CCQ}$	-	$V_{CCQ} + 0.2^{2)}$	V
Input low voltage	V_{IL}	$-0.2^{3)}$	-	$0.2 * V_{CCQ}$	V

- $T_A = -30$ to 85°C , otherwise specified
- Overshoot: $V_{CC} + 1.0$ V in case of pulse width ≤ 20 ns
- Undershoot: -1.0 V in case of pulse width ≤ 20 ns
- Overshoot and undershoot are sampled, not 100% tested.

CAPACITANCE ¹⁾ ($f = 1\text{MHz}$, $T_A = 25^\circ\text{C}$)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C_{IN}	$V_{IN} = 0\text{V}$	-	8	pF
Input/Output capacitance	C_{IO}	$V_{IO} = 0\text{V}$	-	8	pF

- Capacitance is sampled, not 100% tested

DC AND OPERATING CHARACTERISTICS

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input leakage current	I_{LI}	$V_{IN} = V_{SS}$ to V_{CCQ} , $V_{CC} = V_{CCmax}$	-1	-	1	μA
Output leakage current	I_{LO}	$CS\# = V_{IH}$, $OE\# = V_{IH}$ or $WE\# = V_{IL}$, $V_{IO} = V_{SS}$ to V_{CCQ} , $V_{CC} = V_{CCmax}$	-1	-	1	μA
Average operating current	I_{CC1}	Cycle time = 1 μs , $I_{IO} = 0\text{mA}$, 100% duty, $CS\# \leq 0.2\text{V}$, $V_{IN} \leq 0.2\text{V}$ or $V_{IN} \geq V_{CCQ} - 0.2\text{V}$	-	-	5	mA
	I_{CC2}	Cycle time = Min, $I_{IO} = 0\text{mA}$, 100% duty, $CS\# = V_{IL}$, $V_{IN} = V_{IL}$ or V_{IH}	-	-	25	mA
Output low voltage	V_{OL}	$I_{OL} = 0.5\text{mA}$, $V_{CC} = V_{CCmin}$	-	-	$0.2 * V_{CCQ}$	V
Output high voltage	V_{OH}	$I_{OH} = -0.5\text{mA}$, $V_{CC} = V_{CCmin}$	$0.8 * V_{CCQ}$	-	-	V
Standby current (CMOS)	I_{SB}	$CS\# \geq V_{CCQ} - 0.2\text{V}$, Other inputs = 0 ~ V_{CCQ} (Typ. condition : $V_{CC} = 3.0\text{V}$ @ 25°C) (Max. condition : $V_{CC} = 3.3\text{V}$ @ 85°C)	-	-	120	μA

- Maximum I_{CC} specifications are tested with $V_{CC} = V_{CCmax}$.

AC OPERATING CONDITIONS

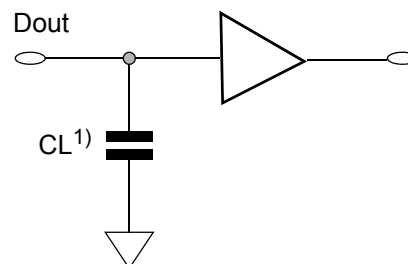
Test Conditions (Test Load and Test Input/Output Reference)

Input Pulse Level : 0.2V to $V_{CCQ}-0.2V$

Input Rise and Fall Time : 5ns

Input and Output reference Voltage : $V_{CCQ}/2$

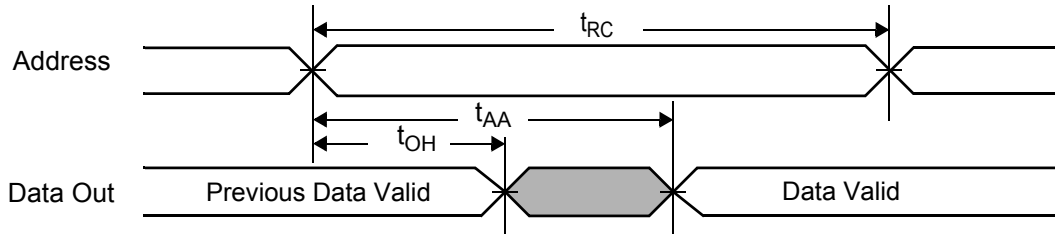
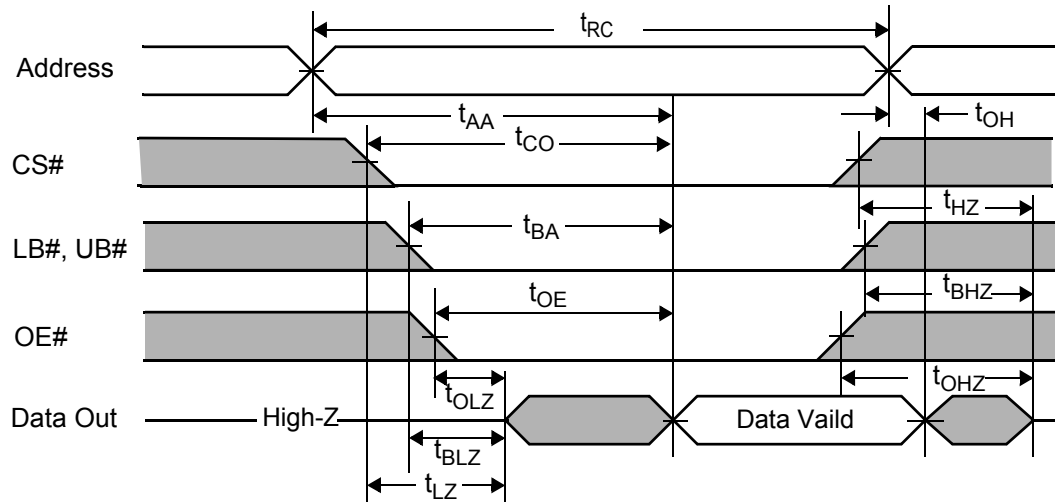
Output Load (See right) : $CL^1) = 30pF$



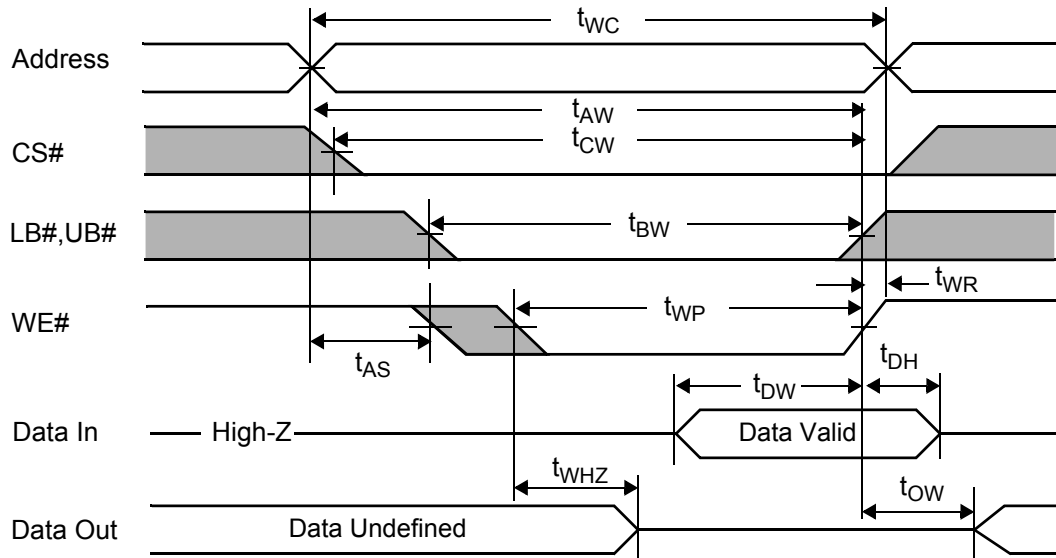
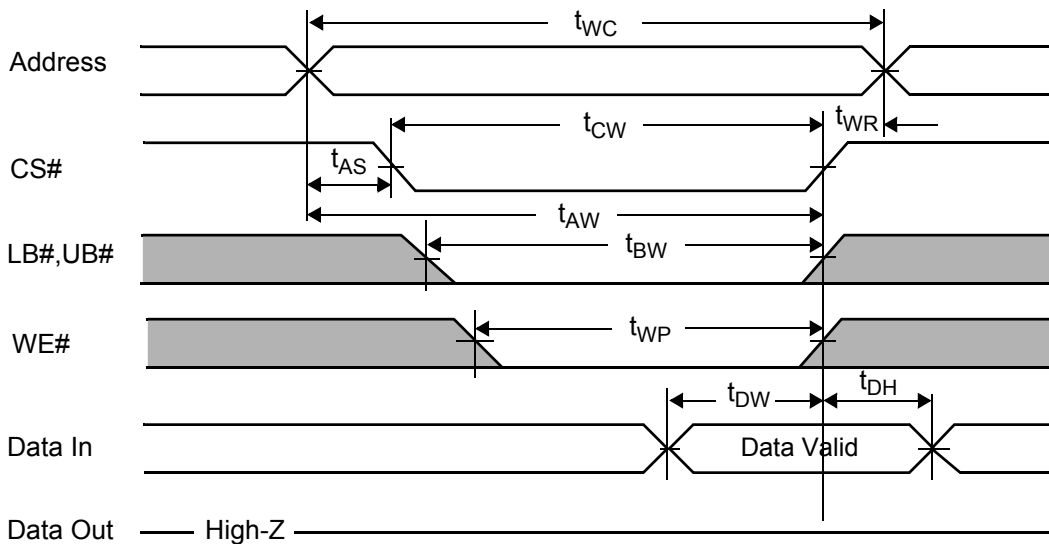
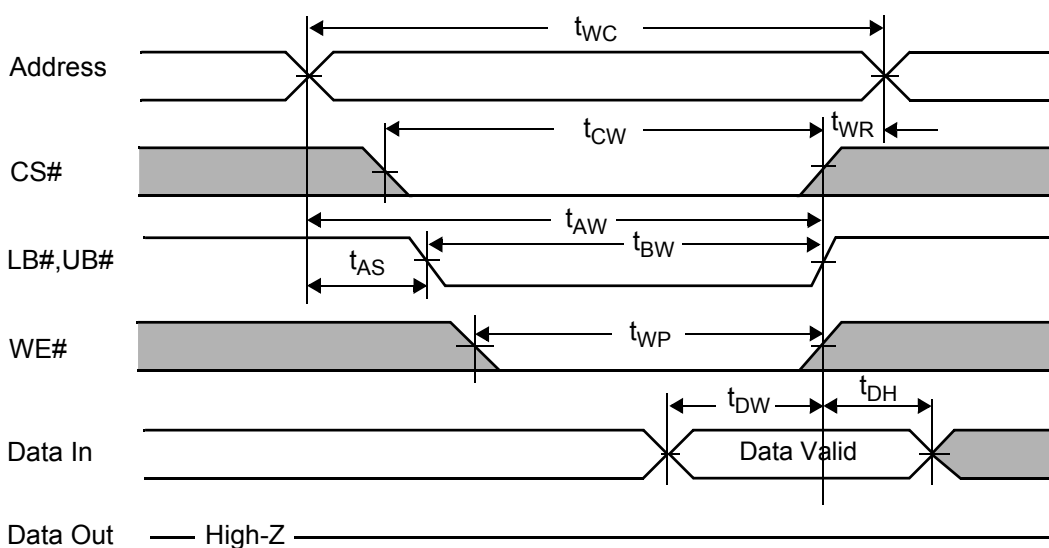
1. Including scope and Jig capacitance

AC CHARACTERISTICS

Parameter List		Symbol	Speed		Unit
			Min	Max	
Read	Read Cycle Time	t_{RC}	70	10k	ns
	Address access time	t_{AA}	-	70	ns
	Chip enable to data output	t_{CO}	-	70	ns
	Output enable to valid output	t_{OE}	-	25	ns
	UB#, LB# enable to data output	t_{BA}	-	25	ns
	Chip enable to low-Z output	t_{LZ}	10	-	ns
	UB#, LB# enable to low-Z output	t_{BLZ}	0	-	ns
	Output enable to low-Z output	t_{OLZ}	0	-	ns
	Chip disable to high-Z output	t_{HZ}	0	20	ns
	UB#, LB# disable to high-Z output	t_{BHZ}	0	20	ns
	Output disable to high-Z output	t_{OHZ}	0	20	ns
	Output hold from Address change	t_{OH}	5	-	ns
	Write	Write Cycle Time	t_{WC}	70	10k
Chip enable to end of write		t_{CW}	60	-	ns
Address setup time		t_{AS}	0	-	ns
Address valid to end of write		t_{AW}	60	-	ns
UB#, LB# valid to end of write		t_{BW}	60	-	ns
Write pulse width		t_{WP}	50	-	ns
Write recovery time		t_{WR}	0	-	ns
Write to output high-Z		t_{WHZ}	0	20	ns
Data to write time overlap		t_{DW}	20	-	ns
Data hold from write time		t_{DH}	0	-	ns
End write to output low-Z		t_{OW}	5	-	ns

TIMING DIAGRAMS
READ CYCLE (1) (Address controlled, CS#=OE#=V_{IL}, WE#=V_{IH}, UB# or/and LB#=V_{IL})

READ CYCLE (2) (WE#=V_{IH})

NOTES (READ CYCLE)

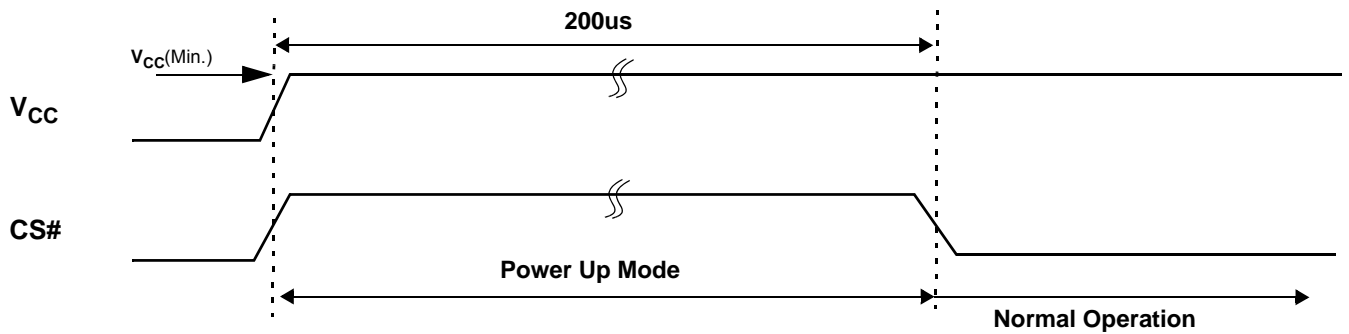
- t_{HZ} , t_{BHZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
- Do not Access device with cycle timing shorter than t_{RC} for continuous periods > 10us.

WRITE CYCLE (1) (WE# controlled)

WRITE CYCLE (2) (CS# controlled)

WRITE CYCLE (3) (UB#/LB# controlled)


NOTES (WRITE CYCLE)

1. A write occurs during the overlap(t_{WP}) of low CS#, low WE# and low UB# or LB#. A write begins at the last transition among low CS# and low WE# with asserting UB# or LB# low for single byte operation or simultaneously asserting UB# and LB# low for word operation. A write ends at the earliest transition among high CS# and high WE#. The t_{WP} is measured from the beginning of write to the end of write.
2. t_{CW} is measured from CS# going low to end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change. t_{WR} applied in case a write ends as CS# or WE# going high.
5. Do not access device with cycle timing shorter than t_{WC} for continuous periods > 10us.

TIMING WAVEFORM OF POWER UP



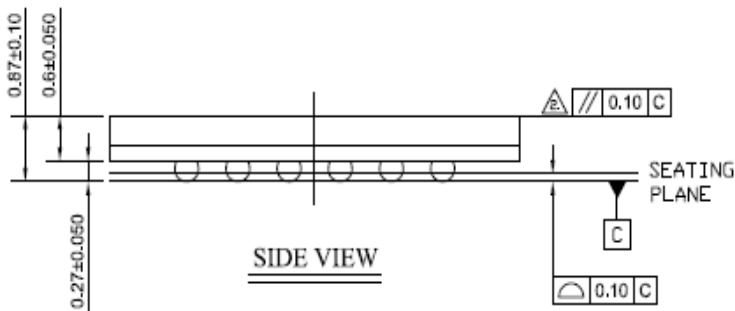
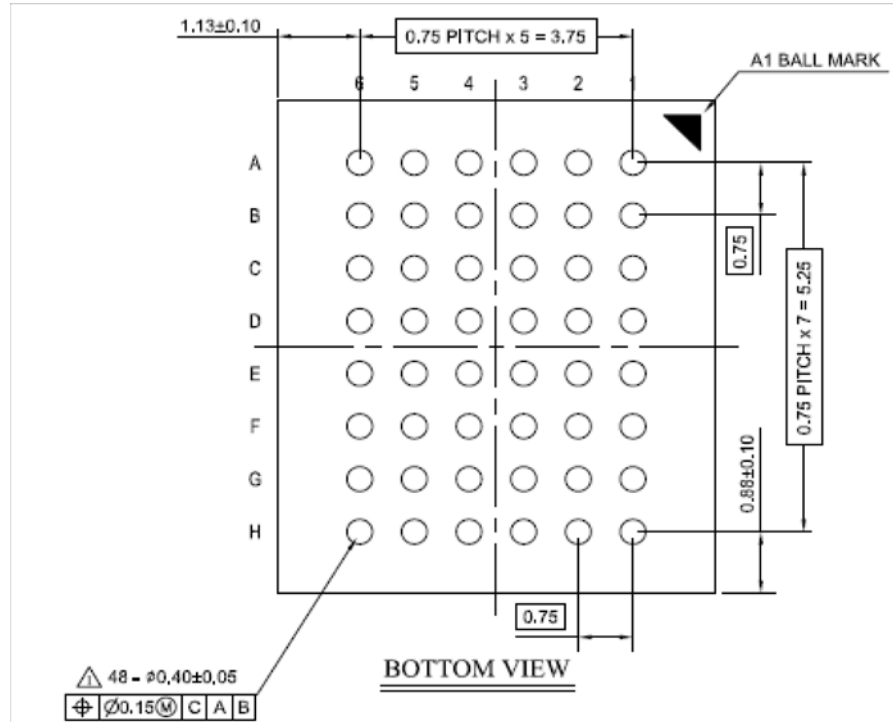
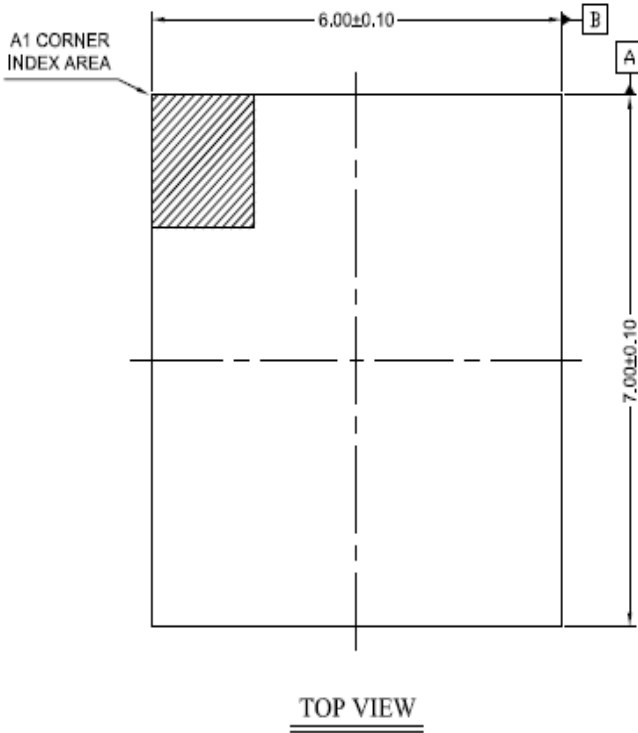
NOTE (POWER UP)

1. After V_{CC} reaches $V_{CC(Min.)}$, wait 200us with CS# high. Then you get into the normal operation.

Unit: millimeters

PACKAGE DIMENSION

48 Ball Fine Pitch BGA (0.75mm ball pitch)



NOTE :

1. ALL DIMENSION ARE IN MILLIMETERS.
2. Δ POST REFLOW SOLDER BALL DIAMETER.
(Pre Reflow Diameter : 0.35 ± 0.02)
3. Δ TOLERANCE INCLUDES WARPAGE.